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(54) **THREE-DIMENSIONAL SEMICONDUCTOR MEMORY DEVICE AND METHOD OF FABRICATING THE SAME**

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(57) **ABSTRACT**

A three-dimensional semiconductor memory device may include a bottom structure and a top structure thereon. The bottom structure may include a semiconductor substrate including a cell array region and a connection region extending therefrom, and a first stack including first gate electrodes and first interlayer insulating layers alternately stacked on the semiconductor substrate. The top structure may include a second stack including second gate electrodes and second interlayer insulating layers alternately stacked on the first stack. Respective lengths of the first gate electrodes in a second direction may decrease as a distance in a first direction increases, and respective lengths of the second gate electrodes in the second direction may increase as a distance in the first direction increases. The first direction may be perpendicular to a bottom surface of the semiconductor substrate, and the second direction may be parallel to the bottom surface of the semiconductor substrate.